

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Overall Thickness	392.00 +/- 5.00 $\mu$ m	ADE, 100%
	5.0	Frontsurface condition	Polished, roughness <5A	Guaranteed by process
	6.0	Total Thickness Variation (TTV)	<5.00 $\mu$ m	Guaranteed by Process
	7.0	Bow	<80.00 $\mu$ m	ADE to ASTM F534, 100%
	8.0	Warp	<80.00 $\mu$ m	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Lasermarking	On wafer BACKSIDE for identification. Scribe format: YYMM-XXXX (unique scribe)	Guaranteed by process
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	380.00 +/- 5.00 $\mu$ m	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	0.007-0.015 Ohmcm	Wafer Vendor
	18.0	Handle Oxygen Concentration	9 - 16 ppma ASTM F121-83	Wafer Vendor
	19.0	Handle Carbon Concentration	<1.0 ppma	Wafer Vendor
	20.0	Backside Finish	Polished with lasermark and no oxide	Wafer Vendor
	BuriedOxide	21.0	Oxide Type	Thermal
22.0		Oxide Thickness	5,000.00 +/- 250.00 A	Nanospec centre point, 4%
23.0		Oxide formed on	Handle Wafer	
DeviceSilicon	24.0	Device Growth Method	CZ	Wafer Vendor
	25.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	26.0	Nominal Thickness	12.00 +/- 1.00 $\mu$ m	Filmetrics, 100% 9-Pt (note3)
	27.0	Distance to device silicon edge from wafer edge	<= 2mm Edge defined	Typical by Process
	28.0	Device Doping Type	P	Wafer Vendor
	29.0	Device Dopant	Boron	Wafer Vendor
	30.0	Device Resistivity	0.007-0.015 Ohmcm	Wafer Vendor
	31.0	Carbon Concentration	<1.0 ppma	Wafer Vendor
	32.0	Oxygen Concentration	9 - 16 ppma ASTM F121-83	Wafer Vendor
	33.0	Voids	none	IR Inspection, 100%
	34.0	Scratches	0	Bright Light, 100% (note 2)

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DeviceSilicon

35.0

Haze

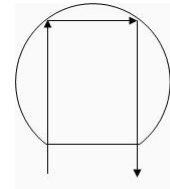
none

Bright Light, 100% (note 2)

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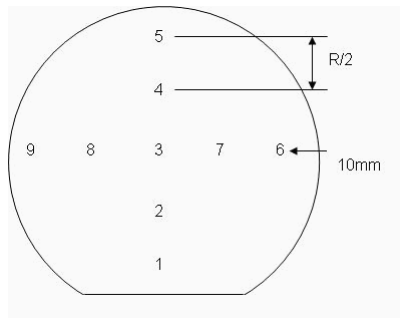
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information